

## Product Summary

$BV_{DSS}$	$R_{DS(ON)}$ max	$I_D$ $T_A = +25^\circ C$
-30V	0.9Ω @ $V_{GS} = -10V$	-0.58A
	1.7Ω @ $V_{GS} = -4.5V$	-0.42A

## Description

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

## Applications

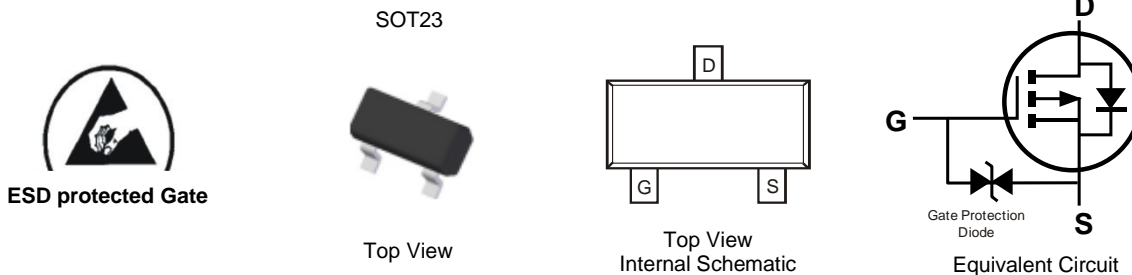
- DC-DC Converters
- Power Management Functions

## Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@www.diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>

## Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208③
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)

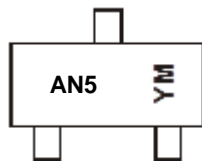


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMP31D7L-7	SOT23	3000/Tape & Reel
DMP31D7L-13	SOT23	10,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



AN5 = Product Type Marking Code  
 YM or  $\bar{Y}M$  = Date Code Marking  
 Y or  $\bar{Y}$  = Year (ex: G = 2019)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026
Code	G	H	I	J	K	L	M	N

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	-30	V
Gate-Source Voltage			$V_{GSS}$	$\pm 20$	V
Continuous Drain Current (Note 6) $V_{GS} = -4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	$I_D$	-0.58 -0.46	A
Maximum Continuous Body Diode Forward Current (Note 6)			$I_S$	-0.52	A
Pulsed Drain Current (10 $\mu\text{s}$ Pulse, Duty Cycle = 1%)			$I_{DM}$	-2.5	A

**Thermal Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			$P_D$	0.43	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		$R_{\theta JA}$	290	$^\circ\text{C/W}$
Total Power Dissipation (Note 6)			$P_D$	0.46	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		$R_{\theta JA}$	270	$^\circ\text{C/W}$
Operating and Storage Temperature Range			$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	-30	—	—	V	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	$I_{DSS}$	—	—	-1	$\mu\text{A}$	$V_{DS} = -24\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 10$	$\mu\text{A}$	$V_{GS} = \pm 16\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	-1	—	-2.6	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	0.4	0.9	$\Omega$	$V_{GS} = -10\text{V}, I_D = -0.42\text{A}$
		—	0.7	1.7		$V_{GS} = -4.5\text{V}, I_D = -0.2\text{A}$
Diode Forward Voltage	$V_{SD}$	—	-0.8	-1.2	V	$V_{GS} = 0\text{V}, I_S = -0.23\text{A}$
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	$C_{ISS}$	—	19	—	pF	$V_{DS} = -15\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	$C_{OSS}$	—	16	—	pF	
Reverse Transfer Capacitance	$C_{RSS}$	—	3	—	pF	
Gate Resistance	$R_g$	—	4.4	—	k $\Omega$	$V_{DS} = V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge	$Q_g$	—	0.36	—	nC	$V_{GS} = -4.5\text{V}, V_{DS} = -10\text{V}, I_D = -250\text{mA}$
Gate-Source Charge	$Q_{gs}$	—	0.1	—	nC	
Gate-Drain Charge	$Q_{gd}$	—	0.1	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	3.3	—	ns	$V_{DD} = -10\text{V}, V_{GS} = -4.5\text{V}, R_L = 47\Omega, R_G = 10\Omega, I_D = -200\text{mA}$
Turn-On Rise Time	$t_R$	—	2.3	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	406	—	ns	
Turn-Off Fall Time	$t_F$	—	237	—	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

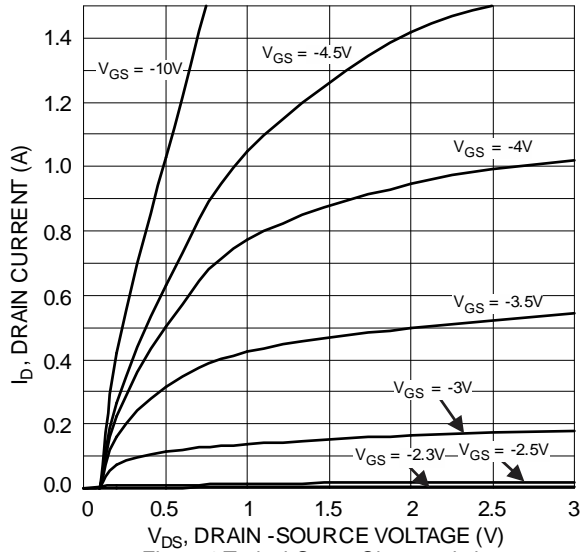


Figure 1 Typical Output Characteristics

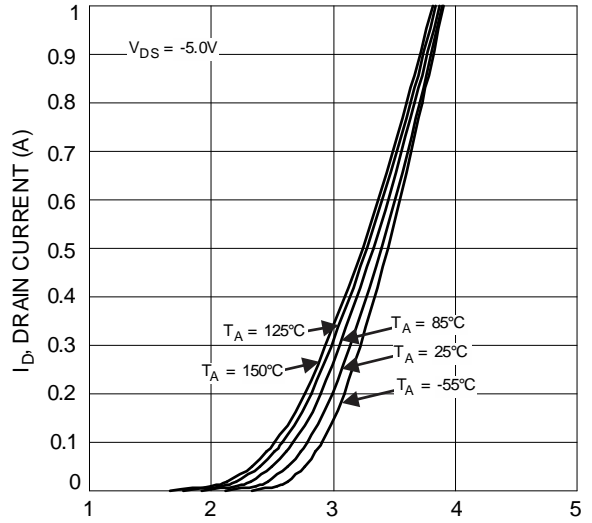


Figure 2 Typical Transfer Characteristics

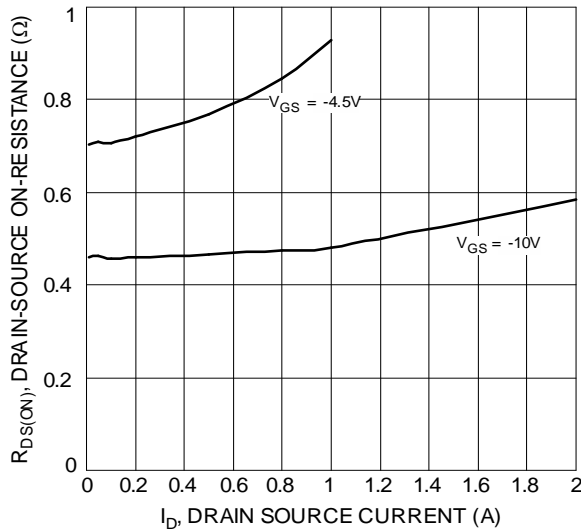


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

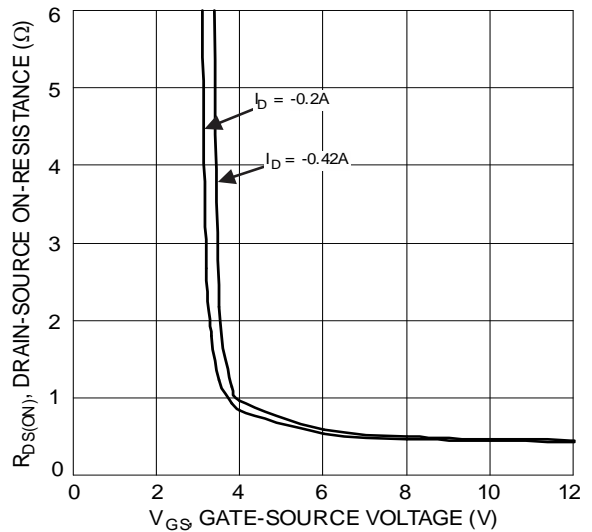


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

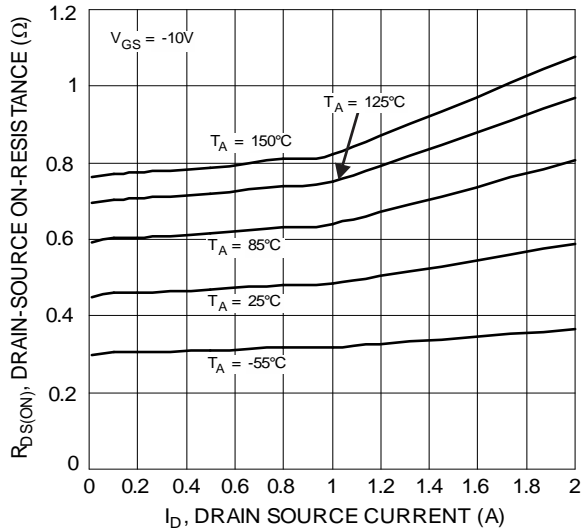


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

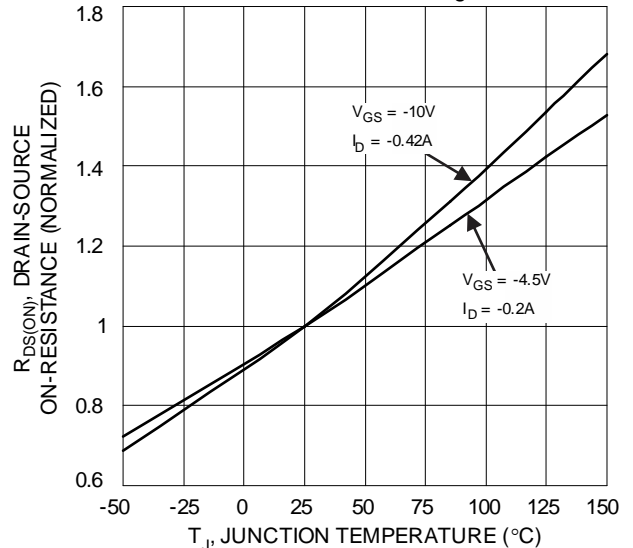


Figure 6 On-Resistance Variation with Temperature

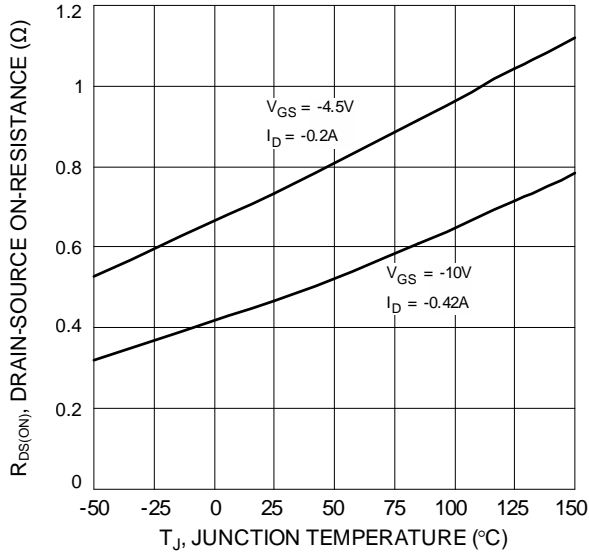


Figure 7 On-Resistance Variation with Temperature

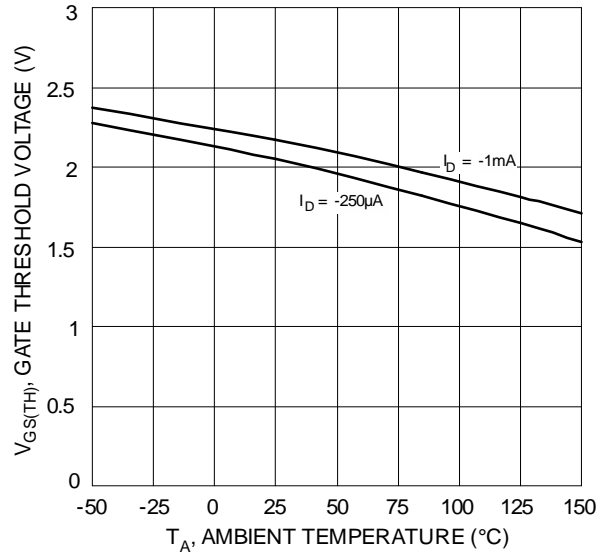


Figure 8 Gate Threshold Variation vs. Ambient Temperature

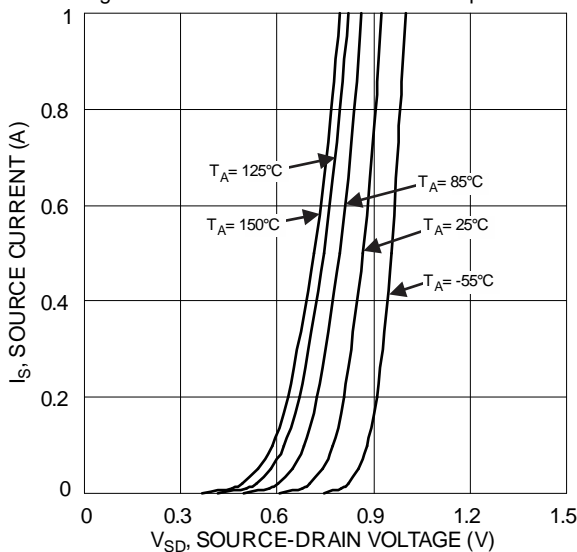


Figure 9 Diode Forward Voltage vs. Current

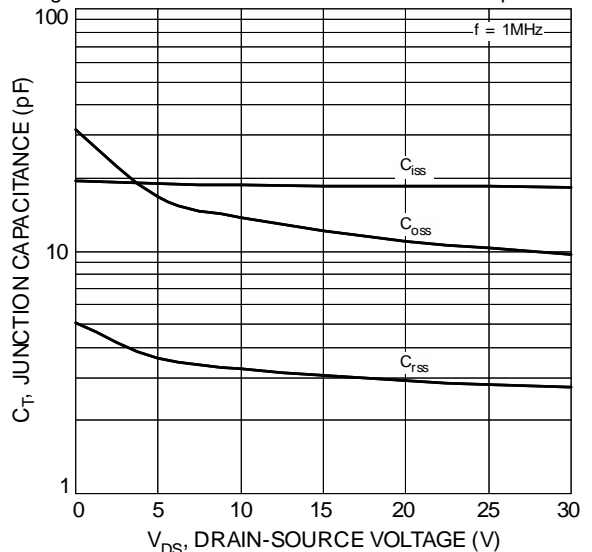


Figure 10 Typical Junction Capacitance

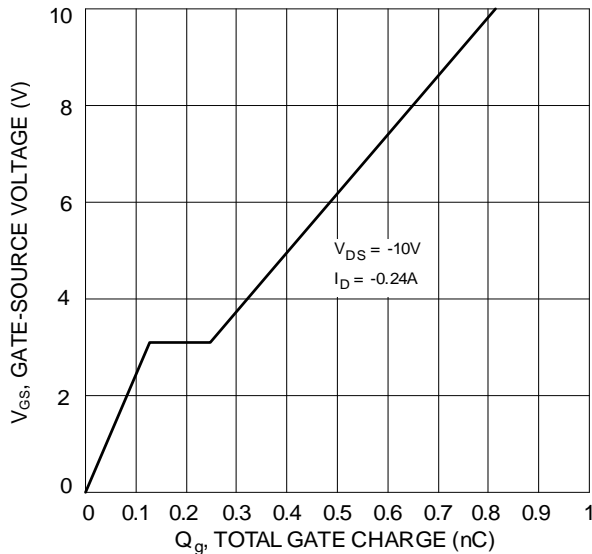


Figure 11 Gate Charge

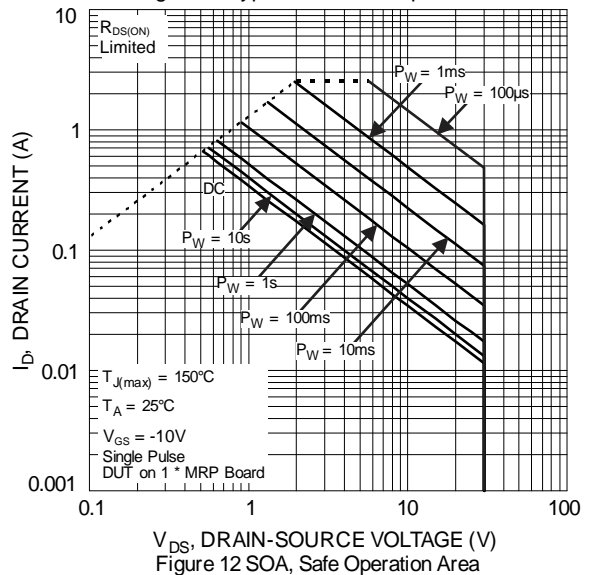
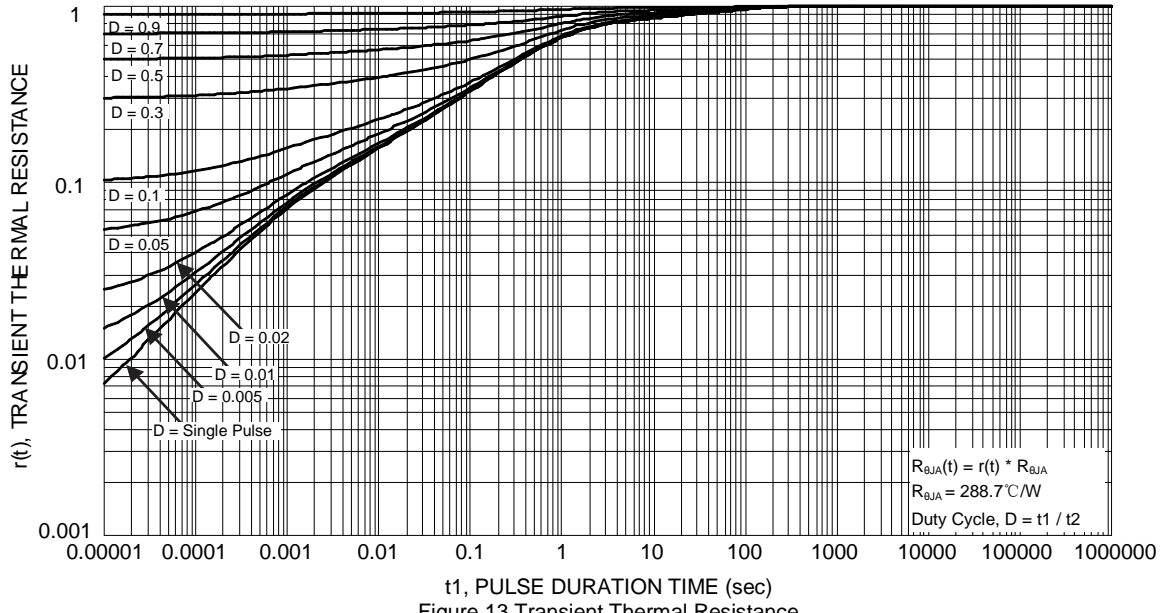


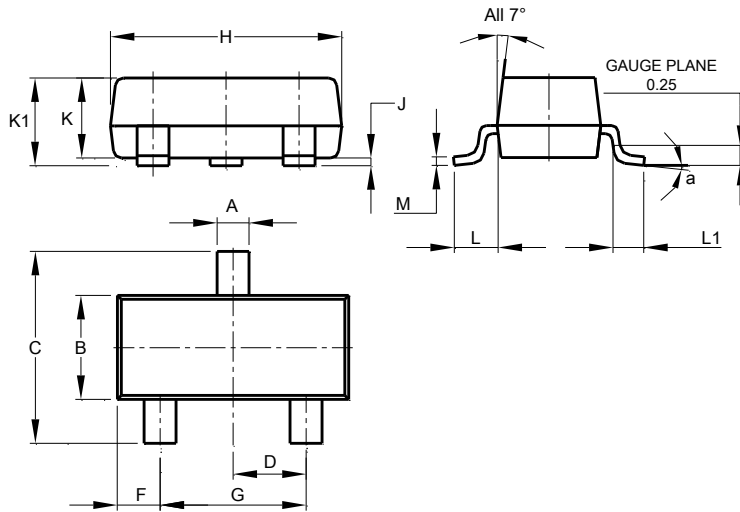
Figure 12 SOA, Safe Operation Area



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23**

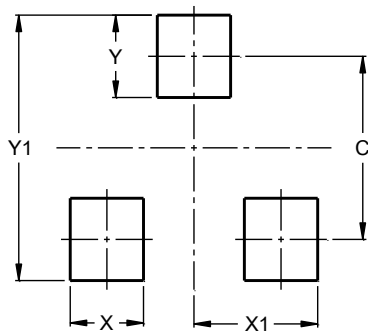


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23**



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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